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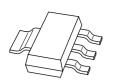
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Kind regards,

Team Nexperia





**PBHV8140Z**500 V, 1 A NPN high-voltage low V<sub>CEsat</sub> (BISS) transistorRev. 01 — 11 December 2009Product data

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

NPN high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9540Z.

#### 1.2 Features

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- AEC-Q101 qualified
- Medium power SMD plastic package

#### 1.3 Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

#### 1.4 Quick reference data

#### **Quick reference data** Table 1.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-	500	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	400	V
I <sub>C</sub>	collector current		-	-	1	А
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA	<u>[1]</u> 100	155	-	

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



# 2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	collector		2, 4
3	emitter		1
4	collector		۲) ع
			sym016

# 3. Ordering information

Table 3. Orde	ring informati	on	
Type number	Package		
	Name	Description	Version
PBHV8140Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

# 4. Marking

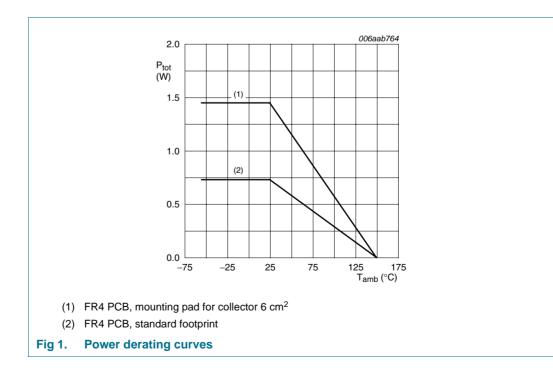
Table 4. Markin	codes
Type number	Marking code
PBHV8140Z	V8140Z

### 5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	500	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	400	V
V <sub>CESM</sub>	collector-emitter peak voltage	$V_{BE} = 0 V$	-	500	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	1	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	2	А
I <sub>BM</sub>	peak base current	single pulse; $t_p \leq 1 \text{ ms}$	-	400	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	0.73	W
			[2] _	1.45	W
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

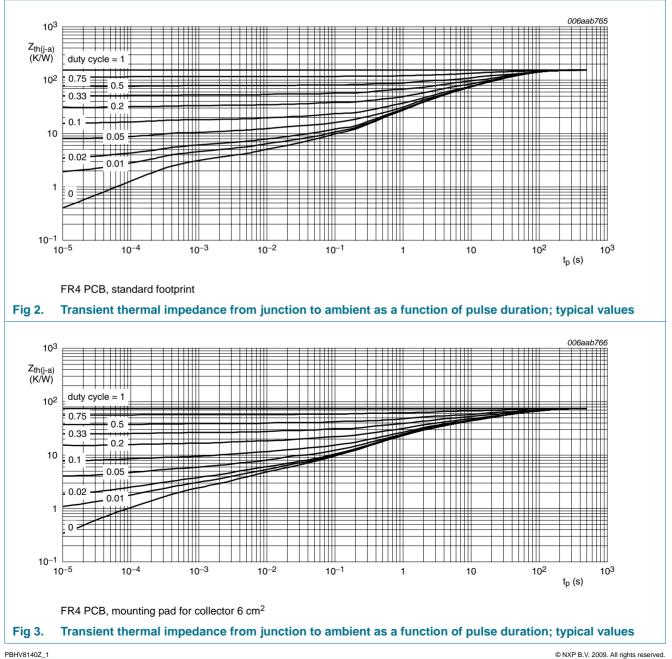


#### Thermal characteristics 6.

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	<u>[1]</u> -	-	170	K/W
	junction to ambient		[2] _	-	85	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>. [2]

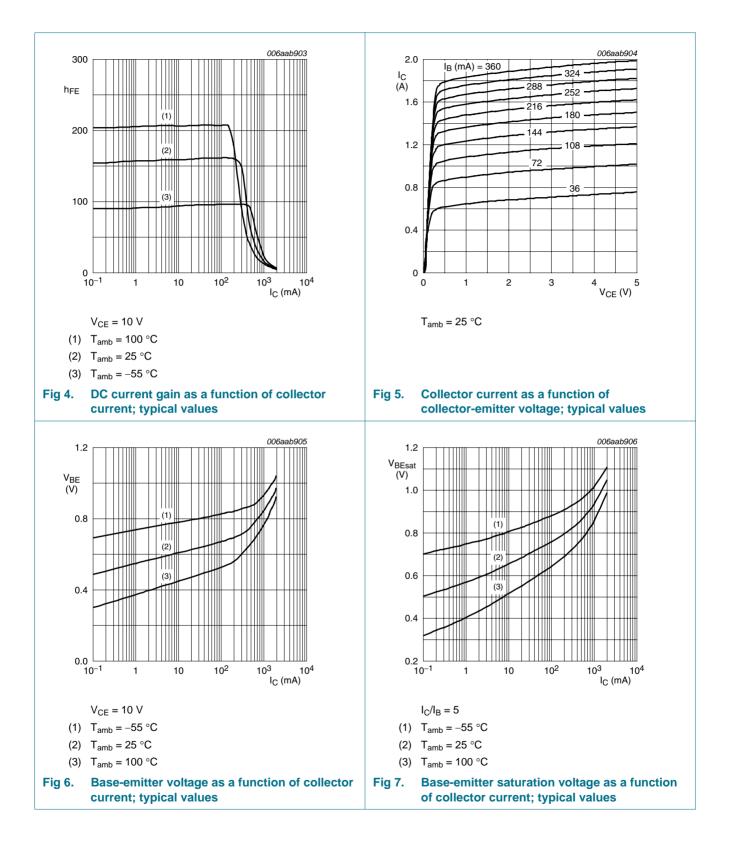


### 7. Characteristics

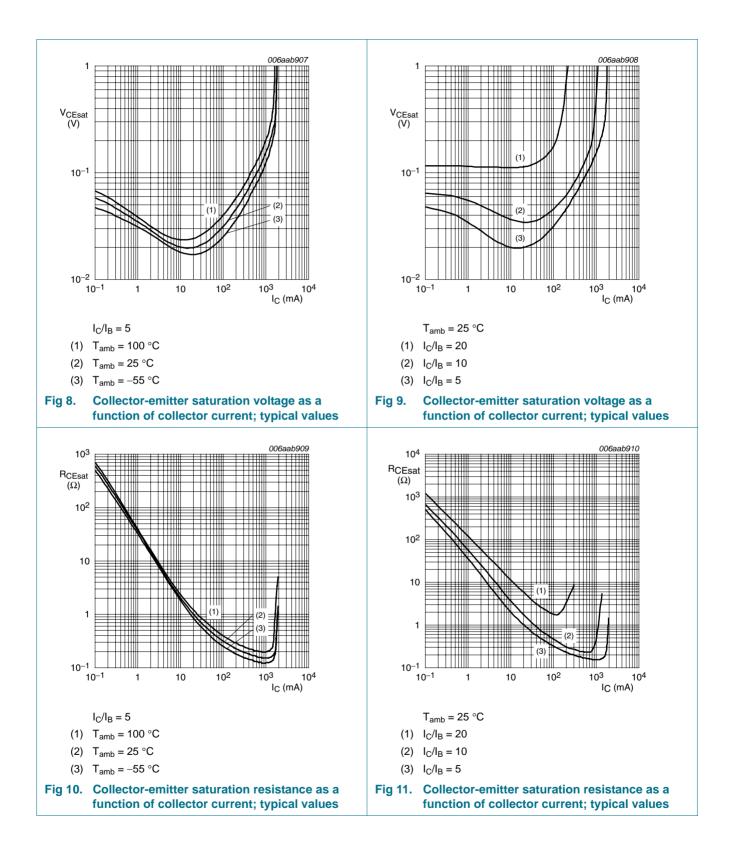
Symbol	Parameter	Conditions	Min	Тур	Max	Uni
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = 320 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
	current	$V_{CB} = 320 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	10	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = 320 \text{ V}; \text{ V}_{BE} = 0 \text{ V}$	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 4 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V				
		I <sub>C</sub> = 50 mA	100	155	-	
		I <sub>C</sub> = 100 mA	<u>[1]</u> 80	150	-	
		I <sub>C</sub> = 500 mA	<mark>[1]</mark> 35	65	-	
		I <sub>C</sub> = 1 A	[ <u>1</u> ] 10	20	-	
V <sub>CEsat</sub>	collector-emitter	$I_{C} = 100 \text{ mA}; I_{B} = 10 \text{ mA}$	<u>[1]</u> _	45	80	mV
	saturation voltage	$I_{C} = 100 \text{ mA}; I_{B} = 20 \text{ mA}$	<u>[1]</u> _	30	50	mV
		I <sub>C</sub> = 500 mA; I <sub>B</sub> = 100 mA	<u>[1]</u> _	85	140	mV
		I <sub>C</sub> = 1 A; I <sub>B</sub> = 200 mA	<u>[1]</u> _	150	250	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = 1 A; I <sub>B</sub> = 200 mA	<u>[1]</u> -	150	250	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C} = 1 \text{ A}; I_{B} = 200 \text{ mA}$	<u>[1]</u> -	0.95	1.1	V
t <sub>d</sub>	delay time	$V_{CC} = 6 \text{ V}; I_{C} = 0.5 \text{ A};$	-	25	-	ns
t <sub>r</sub>	rise time	$I_{Bon} = 0.1 \text{ A}; I_{Boff} = -0.1 \text{ A}$	-	2820	-	ns
t <sub>on</sub>	turn-on time		-	2845	-	ns
t <sub>s</sub>	storage time		-	2585	-	ns
t <sub>f</sub>	fall time		-	1215	-	ns
t <sub>off</sub>	turn-off time		-	3800	-	ns
f <sub>T</sub>	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	-	25	-	MH
C <sub>c</sub>	collector capacitance	$V_{CB} = 20 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A};$ f = 1 MHz	-	12	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = i_c = 0 \text{ A};$ f = 1 MHz	-	600	-	pF

[1] Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02.$ 

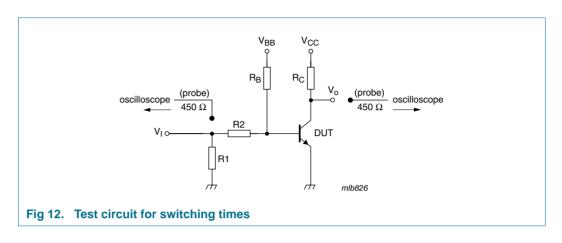
#### 500 V, 1 A NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor



#### 500 V, 1 A NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor



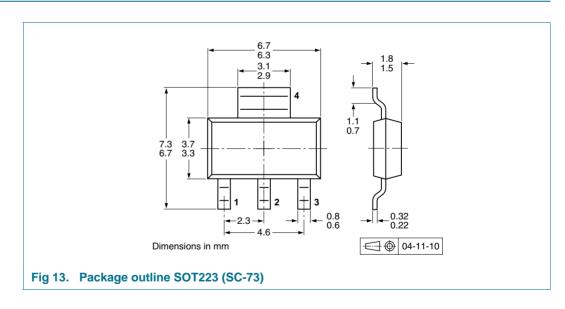
#### 8. Test information



#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



#### **10. Packing information**

#### Table 8. Packing methods

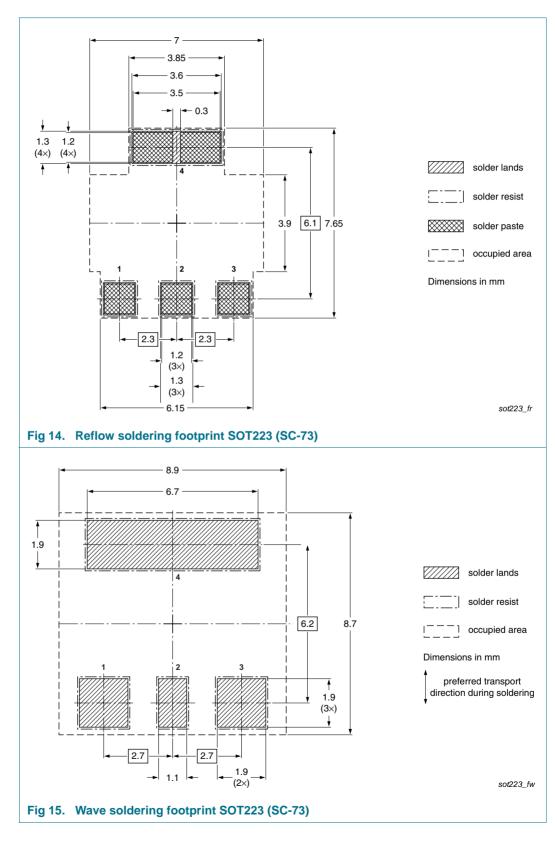
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity
			1000	4000
PBHV8140Z	SOT223	8 mm pitch, 12 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

#### 500 V, 1 A NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 11. Soldering



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PBHV8140Z\_1

# 12. Revision history

Table 9.Revision his	tory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8140Z_1	20091211	Product data sheet	-	-

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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#### 500 V, 1 A NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

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